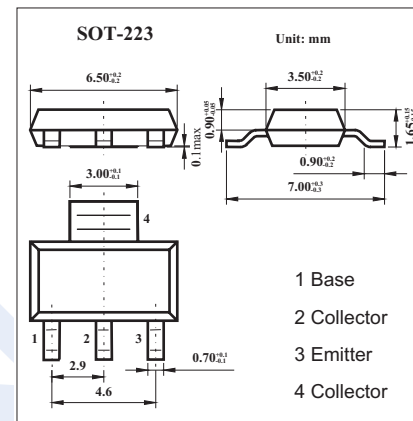


Surface Mount PNP Silicon Power Darlington Transistor KZT127 (CZT127)

■ Features

- High current (max. 5A).
- Low voltage (max. 100V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-100	V
Collector-emitter voltage	V _{CEO}	-100	V
Emitter-base voltage	V _{EB0}	-5	V
Collector current	I _c	-5	A
	I _{CP}	-8	A
Base current	I _B	-120	mA
power dissipation	P _D	2	W
Thermal Resistance.Junction-to-Ambient	R _{θJA}	62.5	°C/W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-65 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to emitter breakdown voltage	V _{CEO}	I _c =-30mA	-100			V
Collector cutoff current	I _{CEO}	V _{CE} =-50V			-500	μ A
Collector cutoff current	I _{CB0}	V _{CB} = -100 V			-200	μ A
Emitter cutoff current	I _{EB0}	V _{EB} = -5.0 V			-2.0	m A
DC current gain	h _{FE}	I _c = -500 mA; V _{CE} = -3.0 V	1000			
		I _c = -3A; V _{CE} = -3.0V	1000			
Collector to emitter saturation voltage	V _{CE(sat)}	I _c = -3.0A; I _B = -12mA			-2.0	V
Base to emitter saturation voltage	V _{BE(sat)}	I _c = -5.0A; I _B = -20mA			-4.0	V
Output capacitance	C _{ob}	V _{CB} = -10 V, I _E = 0, f=1.0MHz			300	pF
Transition frequency	f _T	I _c = -3A; V _{CE} = -4V; f = 1.0 MHz	4.0			MHz